Octal 3-State Inverting Buffer/Line Driver/Line Receiver

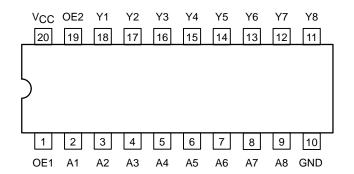
High–Performance Silicon–Gate CMOS

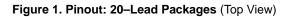
The MC74HC540A is identical in pinout to the LS540. The device inputs are compatible with Standard CMOS outputs. External pull–up resistors make them compatible with LSTTL outputs.

The HC540A is an octal inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HC540A is similar in function to the HC541A, which has noninverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 124 FETs or 31 Equivalent Gates

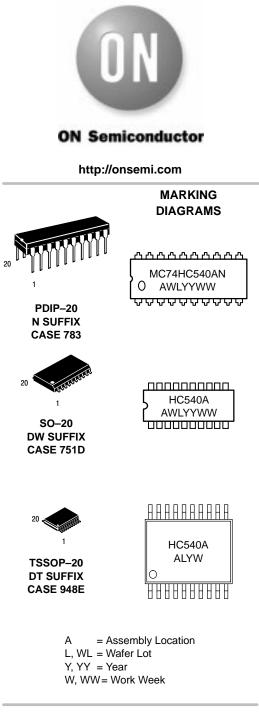




FUNCTION TABLE

| | Inputs | | Output V |
|-----|--------|---|----------|
| OE1 | OE2 | Α | Output Y |
| L | L | L | Н |
| L | L | н | L |
| н | Х | Х | Z |
| Х | Н | Х | Z |

Z = High Impedance X = Don't Care



ORDERING INFORMATION

| Device | Package | Shipping |
|----------------|-----------|-----------|
| MC74HC540AN | PDIP-20 | 1440/Box |
| MC74HC540ADW | SOIC-WIDE | 38/Rail |
| MC74HC540ADWR2 | SOIC-WIDE | 1000/Reel |
| MC74HC540ADT | TSSOP-20 | 75/Rail |
| MC74HC540ADTR2 | TSSOP-20 | 2500/Reel |

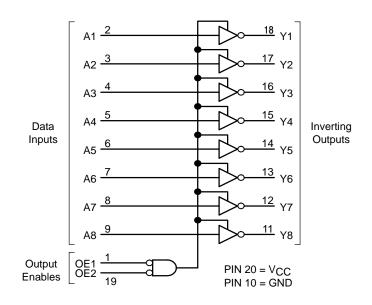


Figure 2. Logic Diagram

MAXIMUM RATINGS (Note 1.)

| Symbol | Pa | rameter | Value | Unit |
|------------------|--|---|-----------------------------------|------|
| VCC | DC Supply Voltage | -0.5 to +7.0 | V | |
| VI | DC Input Voltage | | -0.5 to V _{CC} $+0.5$ | V |
| VO | DC Output Voltage | (Note 2.) | $-0.5 \le V_{O} \le V_{CC} + 0.5$ | V |
| IIK | DC Input Diode Current | | ±20 | mA |
| IOK | DC Output Diode Current | | ±35 | mA |
| IO | DC Output Sink Current | | ±35 | mA |
| ICC | DC Supply Current per Supply Pin | | ±75 | mA |
| IGND | DC Ground Current per Ground Pin | | ±75 | mA |
| T _{STG} | Storage Temperature Range | | -65 to +150 | °C |
| ΤL | Lead Temperature, 1 mm from Case fo | r 10 Seconds | 260 | °C |
| ТJ | Junction Temperature Under Bias | | + 150 | °C |
| θ_{JA} | Thermal Resistance | PDIP SOIC TSSOP | 67 96 128 | °C/W |
| PD | Power Dissipation in Still Air at 85°C | PDIP SOIC TSSOP | 750 500 450 | mW |
| MSL | Moisture Sensitivity | | Level 1 | |
| FR | Flammability Rating | Oxygen Index: 30% – 35% | UL-94-VO (0.125 in) | |
| V _{ESD} | ESD Withstand Voltage | Human Body Model (Note 3.) Machine Model (Note 4.) Charged Device Model (Note 5.) | > 2000 > 200 > 1000 | V |
| LATCH-UP | Latch–Up Performance At | bove V _{CC} and Below GND at 85°C (Note 6.) | ±300 | mA |

1. Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum-rated conditions is not implied.

2. IO absolute maximum rating must be observed.
 3. Tested to EIA/JESD22–A114–A.
 4. Tested to EIA/JESD22–A115–A.

5. Tested to JESD22-C101-A.

6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | | Min | Max | Unit |
|------------------------------------|--|---|-------------|--------------------|------|
| VCC | DC Supply Voltage | (Referenced to GND) | 2.0 | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage | (Referenced to GND) | 0 | VCC | V |
| т _А | Operating Temperature, All Package Types | | - 55 | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time (Figure 3) | V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V | 0 0 0 | 1000 500 400 | ns |

7. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

DC CHARACTERISTICS (Voltages Referenced to GND)

| | | | | vcc | Guara | nteed Lim | nit | |
|-----------------|---|--|---|--------------------------|------------------------------|------------------------------|------------------------------|------|
| Symbol | Parameter | Cond | ition | v | –55 to 25°C | ≤85°C | ≤125°C | Unit |
| VIH | Minimum High–Level Input Voltage | V _{out} = 0.1 V I _{out} ≤ 20 μA | | 2.0 3.0 4.5 6.0 | 1.50 2.10 3.15 4.20 | 1.50 2.10 3.15 4.20 | 1.50 2.10 3.15 4.20 | V |
| VIL | Maximum Low–Level Input Voltage | $V_{out} = V_{CC} - 0.1$ $ I_{out} \le 20 \ \mu A$ | V | 2.0 3.0 4.5 6.0 | 0.50 0.90 1.35 1.80 | 0.50 0.90 1.35 1.80 | 0.50 0.90 1.35 1.80 | V |
| Vон | Minimum High–Level Output Voltage | $V_{in} = V_{IL}$ $ I_{out} \le 20 \ \mu A$ | | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | V _{in} = V _{IL} | I _{out} ≤ 3.6 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA | 3.0 4.5 6.0 | 2.48 3.98 5.48 | 2.34 3.84 5.34 | 2.20 3.70 5.20 | |
| VOL | Maximum Low–Level Output Voltage | V _{in} = VIH I _{out} ≤ 20 μA | | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | V _{in} = VIH | I _{out} ≤ 3.6 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA | 3.0 4.5 6.0 | 0.26 0.26 0.26 | 0.33 0.33 0.33 | 0.40 0.40 0.40 | |
| l _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GNE |) | 6.0 | ±0.1 | ±1.0 | ±1.0 | μΑ |
| I _{OZ} | Maximum Three-State Leakage Current | Output in High Imp V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GN | | 6.0 | ±0.5 | ±5.0 | ±10.0 | μΑ |
| lcc | Maximum Quiescent Supply Current (per Package) | V _{in} = V _{CC} or GNE I _{out} = 0 μA |) | 6.0 | 4 | 40 | 160 | μΑ |

8. Information on typical parametric values can be found in the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

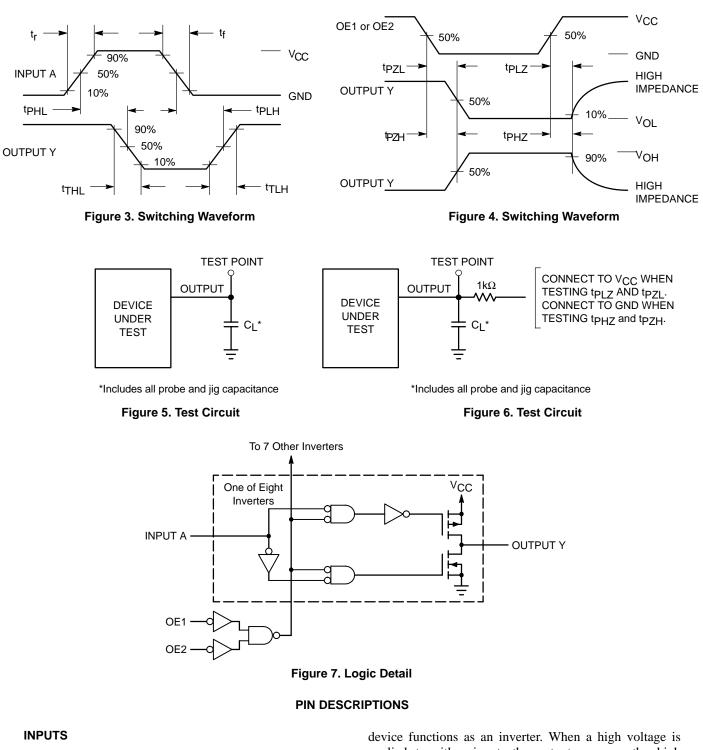
AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

| | | | Guara | anteed Lin | nit | |
|---|---|--------------------------|-----------------------|-----------------------|-----------------------|------|
| Symbol | Parameter | VCC V | –55 to 25°C | ≤85°C | ≤125°C | Unit |
| ^t PLH, ^t PHL | Maximum Propagation Delay, Input A to Output Y (Figures 3 and 5) | 2.0 3.0 4.5 6.0 | 80 30 18 15 | 100 40 23 20 | 120 55 28 25 | ns |
| ^t PLZ [,] ^t PHZ | Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6) | 2.0 3.0 4.5 6.0 | 110 45 25 21 | 140 60 31 26 | 165 75 38 31 | ns |
| ^t PZL [,] ^t PZH | Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6) | 2.0 3.0 4.5 6.0 | 110 45 25 21 | 140 60 31 26 | 165 75 38 31 | ns |
| ttlh, tthl | Maximum Output Transition Time, Any Output (Figures 3 and 5) | 2.0 3.0 4.5 6.0 | 60 22 12 10 | 75 28 15 13 | 90 34 18 15 | ns |
| C _{in} | Maximum Input Capacitance | | 10 | 10 | 10 | pF |
| Cout | Maximum Three-State Output Capacitance (Output in High Impedance State) | | 15 | 15 | 15 | pF |

9. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

| | | Typical @ 25°C, V _{CC} = 5.0 V, V _{EE} = 0 V | |
|------------|---|--|--------|
| | Power Dissipation Capacitance (Per Buffer) (Note 10.) | 35 | pF |
| 10.Used to | determine the no-load dynamic power consumption: $P_D = C_{PD} V$ | CC ² f + ICC VCC. For load considerations, see | the ON |

10. Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).



A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9) Data input pins. Data on these pins appear in inverted form

on the corresponding Y outputs, when the outputs are enabled.

CONTROLS

OE1, OE2 (PINS 1, 19)

Output enables (active-low). When a low voltage is applied to both of these pins, the outputs are enabled and the

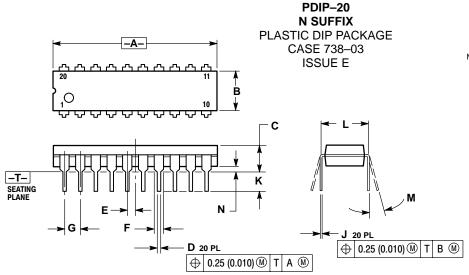
device functions as an inverter. When a high voltage is applied to either input, the outputs assume the high impedance state.

OUTPUTS

Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)

Device outputs. Depending upon the state of the output enable pins, these outputs are either inverting outputs or high–impedance outputs.

PACKAGE DIMENSIONS

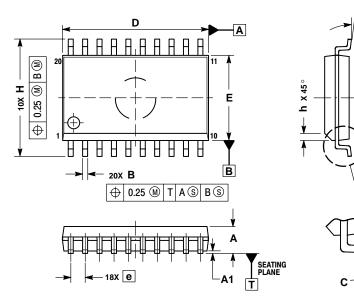


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH. 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL. 4. DIMENSION B DOES NOT INCLUDE MOLD

| | INC | HES | MILLIMETERS | | |
|-----|-----------|-------|-------------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 1.010 | 1.070 | 25.66 | 27.17 | |
| В | 0.240 | 0.260 | 6.10 | 6.60 | |
| С | 0.150 | 0.180 | 3.81 | 4.57 | |
| D | 0.015 | 0.022 | 0.39 | 0.55 | |
| Е | 0.050 | BSC | 1.27 BSC | | |
| F | 0.050 | 0.070 | 1.27 | 1.77 | |
| G | 0.100 | BSC | 2.54 BSC | | |
| J | 0.008 | 0.015 | 0.21 | 0.38 | |
| K | 0.110 | 0.140 | 2.80 | 3.55 | |
| L | 0.300 BSC | | 7.62 | BSC | |
| М | 0 ° | 15° | 0° | 15° | |
| Ν | 0.020 | 0.040 | 0.51 | 1.01 | |

SO-20 **DW SUFFIX** CASE 751D-05 **ISSUE F**

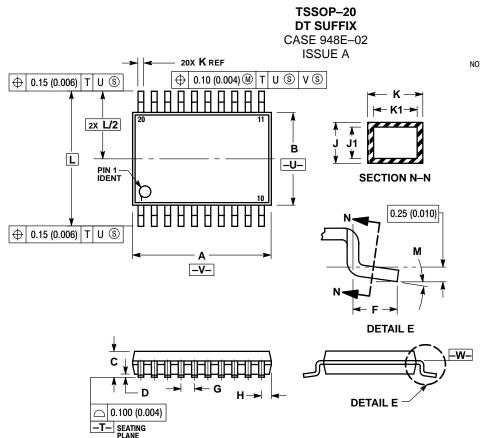


θ

NOTES: 1. DIMENSIONS ARE IN MILLIMETERS. 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994. 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | | | |
|-----|-------------|-------|--|--|
| DIM | MIN | MAX | | |
| Α | 2.35 | 2.65 | | |
| A1 | 0.10 | 0.25 | | |
| В | 0.35 | 0.49 | | |
| С | 0.23 | 0.32 | | |
| D | 12.65 | 12.95 | | |
| Е | 7.40 | 7.60 | | |
| е | 1.27 | BSC | | |
| Н | 10.05 | 10.55 | | |
| h | 0.25 | 0.75 | | |
| L | 0.50 | 0.90 | | |
| θ | 0 ° | 7 ° | | |

PACKAGE DIMENSIONS



| OTES: | |
|-------|---------------------------------------|
| 1. | DIMENSIONING AND TOLERANCING PER ANSI |

- DIMENSIONING AND TOLEMANGING FEB ANGLY
 Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH, PROTRUSIONS OR GATE BURRS. MOLD
 FLASH OR GATE BURRS SHALL NOT EXCEED
 OF 0.000 FED RIDE

- FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.019) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| | MILLIMETERS | | INC | HES | |
|-----|-------------|------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 6.40 | 6.60 | 0.252 | 0.260 | |
| В | 4.30 | 4.50 | 0.169 | 0.177 | |
| С | | 1.20 | | 0.047 | |
| D | 0.05 | 0.15 | 0.002 | 0.006 | |
| F | 0.50 | 0.75 | 0.020 | 0.030 | |
| G | 0.65 | BSC | 0.026 BSC | | |
| Н | 0.27 | 0.37 | 0.011 | 0.015 | |
| J | 0.09 | 0.20 | 0.004 | 0.008 | |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 | |
| K | 0.19 | 0.30 | 0.007 | 0.012 | |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 | |
| L | 6.40 | BSC | 0.252 BSC | | |
| Μ | 0° | 8° | 0° 8° | | |

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